

SPTECH Silicon NPN Power Transistor

DESCRIPTION

- Collector–Emitter Sustaining Voltage
: $V_{CEO(SUS)} = 400V(\text{Min.})$
- Collector Saturation Voltage
: $V_{CE(sat)} = 0.6(\text{Max}) @ I_C = 2.0A$
- Switching Time
: $t_f = 0.9 \mu s(\text{Max.}) @ I_C = 2.0A$

APPLICATIONS

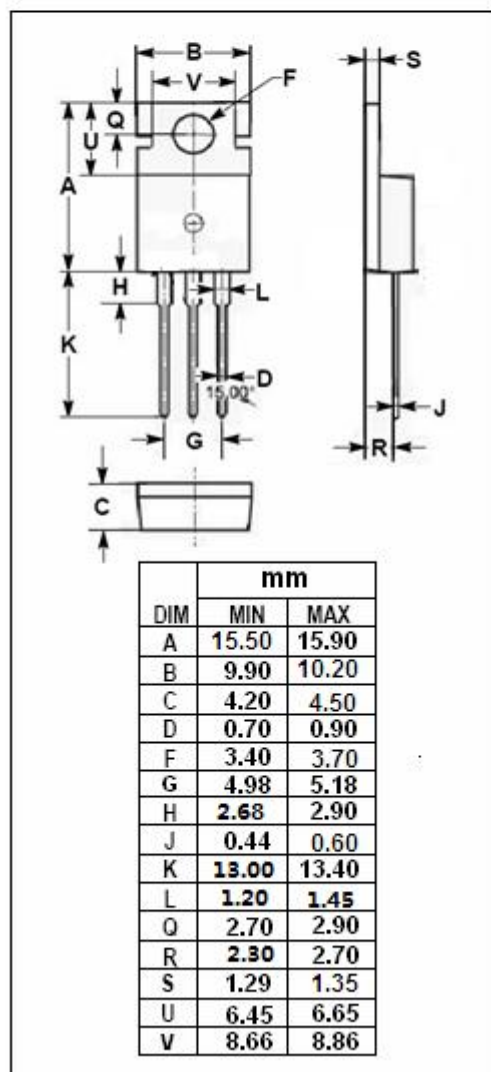
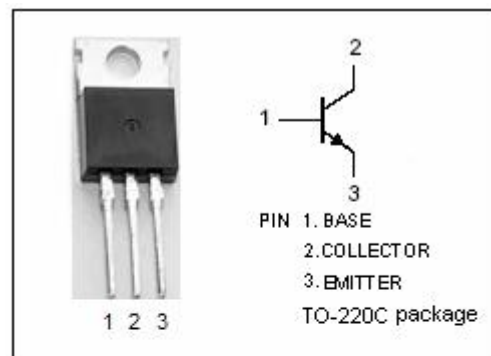
- Designed for use in high-voltage, high-speed, power switching in inductive circuit, they are particularly suited for 115 and 220V switchmode applications such as switching regulators, inverters, Motor controls, Solenoid/Relay drivers and deflection circuits.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEV}	Collector-Emitter Voltage	700	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Collector Current-peak	8	A
I_B	Base Current	2	A
I_{BM}	Base Current-Peak	4	A
I_E	Emitter Current	6	A
I_{EM}	Emitter Current-Peak	12	A
P_C	Collector Power Dissipation $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation $T_C=25^\circ\text{C}$	75	
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.67	$^\circ\text{C/W}$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

$T_C = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = 10\text{mA}; I_B = 0$	400			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = 1\text{A}; I_B = 0.2\text{A}$			0.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = 2\text{A}; I_B = 0.5\text{A}$			0.6	V
$V_{CE(sat)-3}$	Collector-Emitter Saturation Voltage	$I_C = 4\text{A}; I_B = 1\text{A}$			1.0	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	$I_C = 1\text{A}; I_B = 0.2\text{A}$			1.2	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	$I_C = 2\text{A}; I_B = 0.5\text{A}$			1.6	V
I_{CEV}	Collector Cutoff Current	$V_{CEV} = 700\text{V}; V_{BE(off)} = 1.5\text{V}$ $T_C = 100^\circ\text{C}$			1 5	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 9\text{V}; I_C = 0$			1	mA
h_{FE-1}	DC Current Gain	$I_C = 1\text{A}; V_{CE} = 5\text{V}$	10		60	
h_{FE-2}	DC Current Gain	$I_C = 2\text{A}; V_{CE} = 5\text{V}$	8		40	
f_T	Current-Gain—Bandwidth Product	$I_C = 0.5\text{A}; V_{CE} = 10\text{V};$	4			MHz
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = 10\text{V}; f_{test} = 0.1\text{MHz}$		65		pF